

Process Change Notice

Parts Affected:

Chip process CPD41, High Current Switching Diode discrete semiconductors, wafers, and die in chip form.

Extent of Change:

An overall reduction of the die area.

The CPD41 chip process currently measures 20 x 20 mils and is being replaced by the CPD93V chip process which measures 12.8 x 12.8 mils.

Reason for Change:

To accommodate assemblies of extremely small surface mount, epoxy molded packages.

Effect of Change:

This change does not affect the electrical characteristics of any device.

Effective Date of Change:

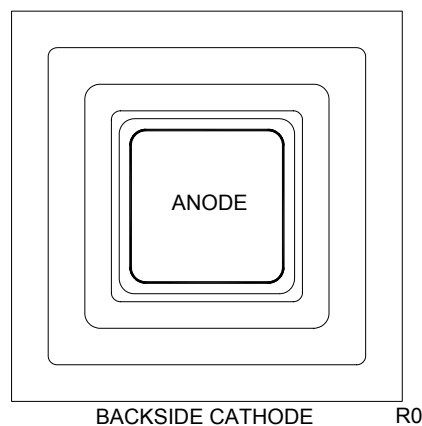
Existing inventory will be shipped until depleted.

Sample Availability:

Please contact Salesperson or Manufacturer's Representative.

Figures:

CPD93V Chip Geometry



Die Size:	12.8 x 12.8 mils
Die Thickness:	7.1 mils
Bond Pad Area (Anode):	5.1 x 5.1 mils
Topside Metal:	Al (30,000Å)
Backside Metal:	Au.As/Au (10,000Å)



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PCN # 109

Notification Date:

21 April 2009

Part Numbers Affected:

CPD41-BAS56-WN
CPD41-CEN923-CT
CPD41-CMPD4150-WR
CPD41-CMPD4150-WS
CPD41-CMPD914-WN
CPD41-1N3600-WN
CPD41-1N4148-CT
CPD41-1N4150-CT
CPD41-1N4150-WN

CMPD4150
CMHD4150
BAS56